Elektronische Bauelemente

2SB1658

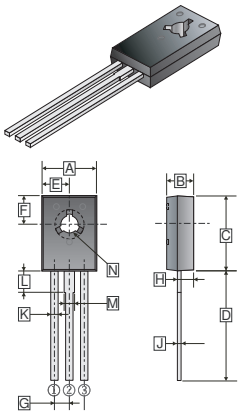
PNP General Purpose Transistor

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead free

FEATURES

- High Current
- Amplifier and Switching Applications

TO-126



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	7.40	7.80	H	1.10	1.50
B	2.50	2.90	J	0.45	0.60
C	10.60	11.00	K	0.66	0.86
D	15.30	15.70	L	2.10	2.30
E	3.70	3.90	M	1.17	1.37
F	3.90	4.10	N	3.00	3.20
G	2.29 TYP.				

ABSOLUTE MAXIMUM RATINGS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Collector - Base Voltage	V_{CBO}	-30	V
Collector - Emitter Voltage	V_{CEO}	-30	V
Emitter - Base Voltage	V_{EBO}	-6	V
Collector Current -Continuous	I_C	-5	A
Collector Power Dissipation	P_C	1	W
Maximum Junction to Ambient	$R_{\theta JA}$	125	℃ / W
Junction, Storage Temperature	T_J, T_{STG}	150, -55 ~ 150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃ unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-30	-	-	V	I_C= -0.1mA, I_E=0
Collector-Emitter Breakdown voltage	$V_{(BR)CEO}$	-30	-	-	V	I_C= -1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-	-	V	I_C=0, I_E= -0.1mA
Collector Cut-Off Current	I_{CBO}	-	-	-0.1	μA	V_{CB}= -30V, I_E= 0
Emitter Cut-Off Current	I_{EBO}	-	-	-0.1	μA	V_{EB}= -6V, I_C= 0
DC Current Gain	$h_{FE(1)}$	150	-	600		V_{CE}= -2V, I_C= -1A
	$h_{FE(2)}$	50	-	-		V_{CE}= -2V, I_C= -4A
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	-	-	-0.15	V	I_C= -1A, I_B = -50mA
	$V_{CE(sat)2}$	-	-	-0.25		I_C= -2A, I_B = -100mA
	$V_{CE(sat)3}$	-	-	-0.5		I_C= -4A, I_B = -200mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	-	-	-1.5	V	I_C= -1A, I_B = -100mA
Transition frequency	f_T	-	95	-	MHz	V_{CE}= -10V, I_C= -50mA
Collector output capacitance	C_{ob}	-	100	-	pF	V_{CB}= -10V, I_E= 0, f=1MHz